

METHODS OF FABRICATING MOS FIELD EFFECT TRANSISTORS WITH POCKET REGIONS

Abstract of the Disclosure

5 MOSFETs with pocket regions are fabricated. A gate electrode layer is formed
on a semiconductor substrate; and lightly doped drain regions are formed in the
semiconductor substrate adjacent the gate electrode layer. A blocking pattern is
formed on the semiconductor substrate where the gate electrode layer is formed. The
blocking pattern is adjacent and spaced apart from the gate electrode layer a
predetermined distance and exposes portions of the semiconductor substrate adjacent
10 sidewalls of the gate electrode layer. Pocket regions are formed in the semiconductor
substrate by implanting impurity ions using the gate electrode layer and the blocking
pattern as an ion implantation mask.